DRAM DDR2

SODIMM

| RDIMM | UDIMM | **SODIMM** | mini DIMM |

DDR2 has been the standard memory solutions for applications in virtually all market segments from Servers, PCs and Notebooks to Printers, Networking and Storage systems and many more for several years providing superior cost and performance criteria. DDR2 has started to relinquish its role as the memory industry's mainstream technology to DDR3 and is forecasted to become a legacy product by early 2011

Available in power supply voltages of 1.8V (and 1.55V for FBDIMMs) and with transfer data rates from 400Mb/s to 800Mb/s and beyond, DDR2 has been designed in a wide range of applications providing designers with numerous module options to choose from. Wintec offers a wide range of DDR2 Module solutions. Please click on the link to find out more about our solutions.

more images

DDR2 - 200-Pin SODIMM - Registered ECC

Standard Profile (1.181") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD2AE01GX809-xxxx-yyz	1 rank	128x72	128Mx8	1.8V
2GB	WD2AE02GX809-xxxx-yyz	1 rank	256x72	256Mx8	1.8V
4GB	WD2AE04GD809-xxxx-yyz	2 rank	512x72	512Mx8	1.8V

DDR2 - 200-Pin SODIMM - Unbuffered ECC

Standard Profile (1.181") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD2SE01GX809-xxxx-yy	1 rank	128x72	128Mx8	1.8V

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
2GB	WD2SE02GX818-xxxx-yy	2 rank	256x72	128Mx8	1.8V
	WD2SE02GX809-xxxx-yy	1 rank	256x72	256Mx8	1.8V
4GB	WD2SE04GX818-xxxx-yy	2 Rank	512x72	256Mx8	1.8V

DDR2 - 200-Pin SODIMM - Unbuffered Non-ECC

Standard Profile (1.181") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD2SN01GX808-xxxx-yy	1 rank	128x64	128Mx8	1.8V
2GB	WD2SN02GX816-xxxx-yy	2 rank	256x64	128Mx8	1.8V
	WD2SN02GX808-xxxx-yy	1 rank	256x64	256Mx8	1.8V
4GB	WD2SN04GX816-xxxx-yy	2 rank	512x64	256Mx8	1.8V
	WD2SN04GX808-xxxx-yy	1 rank	512x64	512Mx8	1.8V

(xxxxx) Modules Speed (MHz) and CAS Latency
= 800I: 800MHz CL6
800G : 800MHz CL5
667G : 667MHz CL5
533E : 533MHz CL4

DRAM Manufacturer and Die Revision
(yy) = P: Samsung   A: A-Die
H: Micron   B: B-Die
C: Hynix   C: C-Die

Buffer / Register set (Only applies to Registered/Buffered modules)
(z) = I: Inphi
D: IDT
L: Intel